

ABSTRACT

A method of forming a Bi-layered superlattice material on a substrate using chemical vapor deposition of a precursor solution of trimethylbismuth and a metal compound dissolved in an organic solvent. The precursor solution is heated and vaporized prior

5 to deposition of the precursor solution on an integrated circuit substrate by chemical vapor deposition. No heating steps including a temperature of 650°C or higher are used.

2000/2001
10/2002